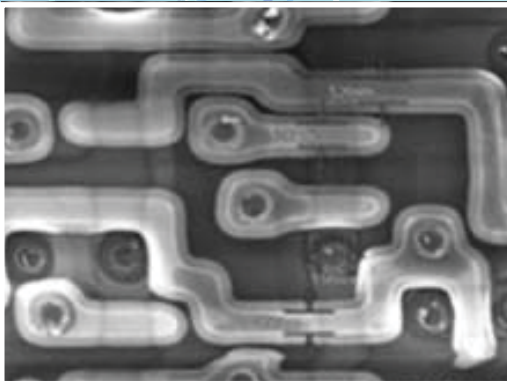
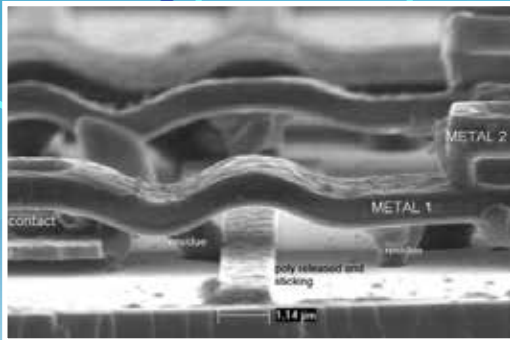


複合式高密度電漿蝕刻機

csun

High density plasma etcher

PREE-BIR2010 / BI2R2010



機台特點 Characteristics

- 高密度電漿源(ICP)實現高速電漿蝕刻
High density plasma source (ICP) achieves high etching rate.
- Loadlock設計可以有效穩定製程環境並避免人員接觸有害氣體
The Loadlock design effectively stabilizes the process environment and prevents personnel from coming into contact with harmful gases.
- 8"載具提供小尺寸試片彈性放置
8 inch carrier provides flexible placement of small size test pieces.
- 特殊載具設計，避免Partical汙染試片
Special carrier design can reduce particle pollution.
- 滿足鈍化層、氧化物、氮化物、碳化矽、矽蝕刻以及碳渣清潔的製程需求
Requirements for passivation, oxide, nitride, silicon carbide, silicon etching, and carbon cleaning processes can be met.
- 高密度電漿配合高效率真空系統設計(Loadlock)，節省時間提高產能
High density plasma with high efficiency vacuum system design (Loadlock) to gain higher throughput.



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Leading in Thermal and UV Light Processing Equipment

PREE-BIR2010 / BI2R2010 反應式離子蝕刻機

設備電力規格 Power	220V 3φ 50/60 Hz 24kVA
腔體材質 Material of chamber	SUS
電漿源 Plasma source	ICP mode RIE mode (bias) Dual source (ICP, bias)
射頻電源電力規格 Generator power	13.56 MHz, 2kW (ICP) 13.56 MHz, 1kW (RIE) (PREE-BIR2010) 13.56 MHz, 2kW (ICP) 2 MHz, 1kW (RIE) (PREE-BI2R2010)
製程氣體 Process gas	O ₂ 、Ar、CHF ₃ 、C ₂ F ₆ 、SF ₆ (Max. 7 gas lines)
氣體流量控制 Gas flow control	MFC (±1% of set point) <small>註: 流量設定 ≥ 全流量40%, 控制精度為 ±1% of set point, <40%時控制精度為 ±0.4% of full scale Note: Control accuracy ±1% of set point when flow rate ≥40%, control accuracy ±0.4% of full scale when flow rate <40%</small>
泵浦規格 Standard pump	Dry pump, pumping speed >90 cfm @60 Hz Turbopump, N ₂ pumping speed > 500 l/s
製程壓力計 Pressure gauge	Capacitive pressure sensor
製程壓力控制 EQ pressure	10 ~ 100 mTorr
控制系統 Control system	20.5 inch TFT panel / PC / Windows 10
設備尺寸 Dimension	W1500mm x D1300mm x H2300mm
載台溫度控制 Stage temperature controller	chiller
規範 Compliance	SEMI S2-01, SEMI S8-01

Due to C SUN continuing efforts to improve their systems, these specifications are subject to change without notice.
受長期研發需要，本公司保有規格修改之權利，恕不另行通知

DM2023Q3-000-TW

晶片逆向分析應用 IC reverse analysis application

- | | |
|--|--|
| <p>1. 鈍化層蝕刻
Passivation etch</p> <p>2. 氧化矽蝕刻
Silicon oxide etch</p> <p>3. 氮化矽蝕刻
Silicon nitride etch</p> | <p>4. 碳化矽蝕刻
Silicon carbide etch</p> <p>5. 矽蝕刻
Silicon etch</p> <p>6. 碳渣清潔
Carbon cleaning</p> |
|--|--|

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